

# 2SB935, 2SB935A

## Silicon PNP epitaxial planar type

For low-voltage switching

### Features

- Low collector to emitter saturation voltage  $V_{CE(sat)}$
- High-speed switching
- N type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.

### Absolute Maximum Ratings ( $T_C=25^\circ\text{C}$ )

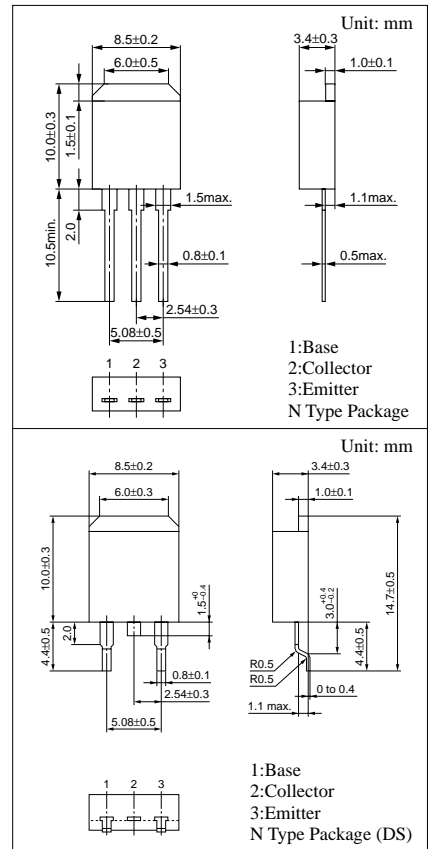
Parameter	Symbol	Rated	Unit
Collector to base voltage	$V_{CBO}$	-40	V
2SB935A		-50	
Collector to emitter voltage	$V_{CEO}$	-20	V
2SB935A		-40	
Emitter to base voltage	$V_{EBO}$	-5	V
Peak collector current	$I_{CP}$	-15	A
Collector current	$I_C$	-10	A
Collector power dissipation	$P_C$	35	W
$T_C=25^\circ\text{C}$ $T_a=25^\circ\text{C}$		1.3	
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

### Electrical Characteristics ( $T_C=25^\circ\text{C}$ )

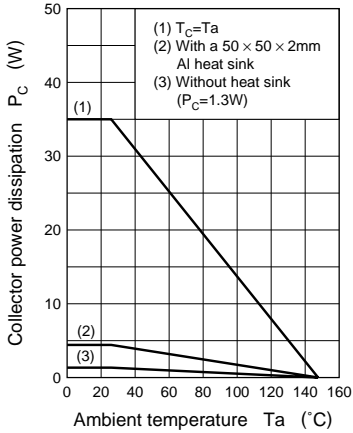
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = -40\text{V}, I_E = 0$			-50	$\mu\text{A}$
2SB935A		$V_{CB} = -50\text{V}, I_E = 0$			-50	
Emitter cutoff current	$I_{EBO}$	$V_{EB} = -5\text{V}, I_C = 0$			-50	$\mu\text{A}$
Collector to emitter voltage	$V_{CEO}$	$I_C = -10\text{mA}, I_B = 0$	-20			V
2SB935A			-40			
Forward current transfer ratio	$h_{FE1}$	$V_{CE} = -2\text{V}, I_C = -0.1\text{A}$	45			
	$h_{FE2}^*$	$V_{CE} = -2\text{V}, I_C = -2\text{A}$	90		260	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -7\text{A}, I_B = -0.23\text{A}$			-0.6	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = -7\text{A}, I_B = -0.23\text{A}$			-1.5	V
Transition frequency	$f_T$	$V_{CE} = -10\text{V}, I_C = -0.5\text{A}, f = 10\text{MHz}$		150		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$		200		pF
Turn-on time	$t_{on}$	$I_C = -2\text{A}, I_{B1} = -66\text{mA}, I_{B2} = 66\text{mA}$		0.1		$\mu\text{s}$
Storage time	$t_{stg}$		0.5		$\mu\text{s}$	
Fall time	$t_f$		0.1		$\mu\text{s}$	

\* $h_{FE2}$  Rank classification

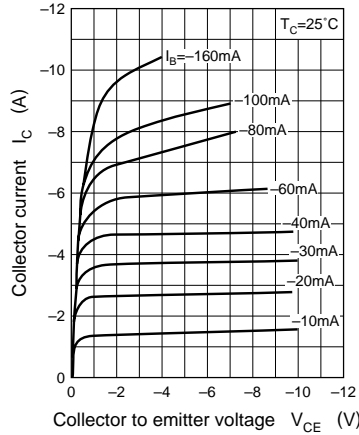
Rank	Q	P
$h_{FE2}$	90 to 180	130 to 260



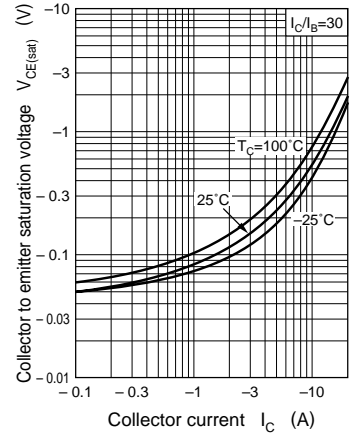
$P_C - T_a$



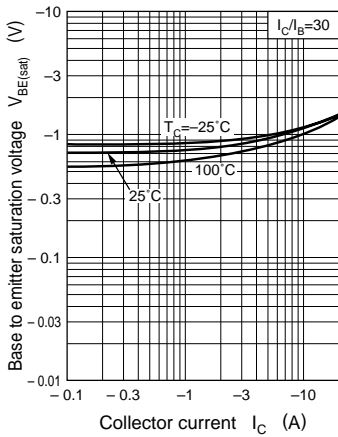
$I_C - V_{CE}$



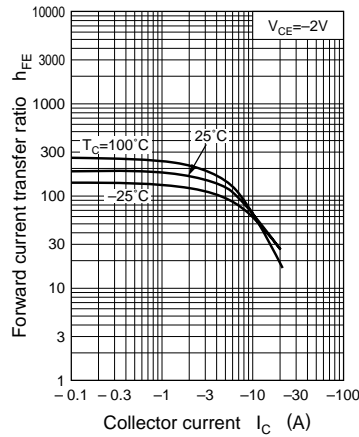
$V_{CE(sat)} - I_C$



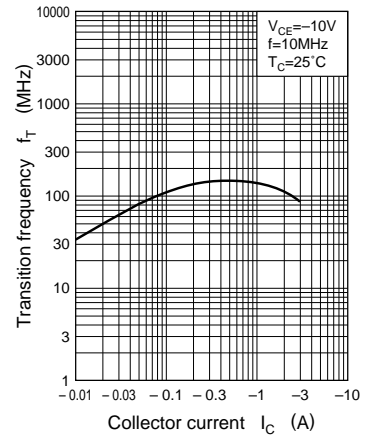
$V_{BE(sat)} - I_C$



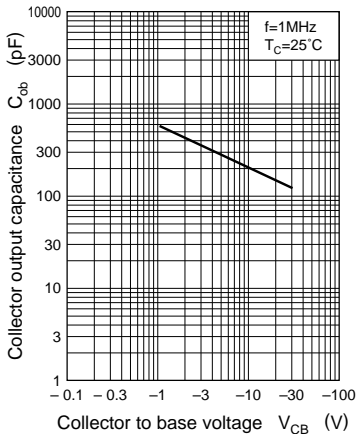
$h_{FE} - I_C$



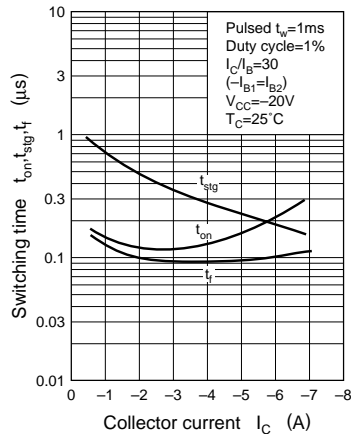
$f_T - I_C$



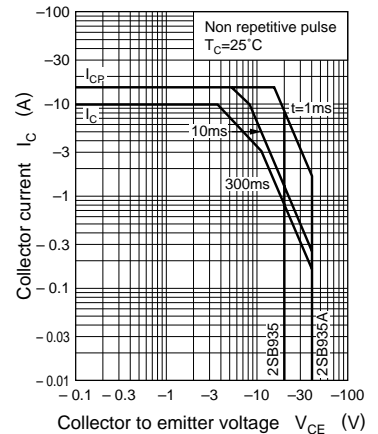
$C_{ob} - V_{CB}$

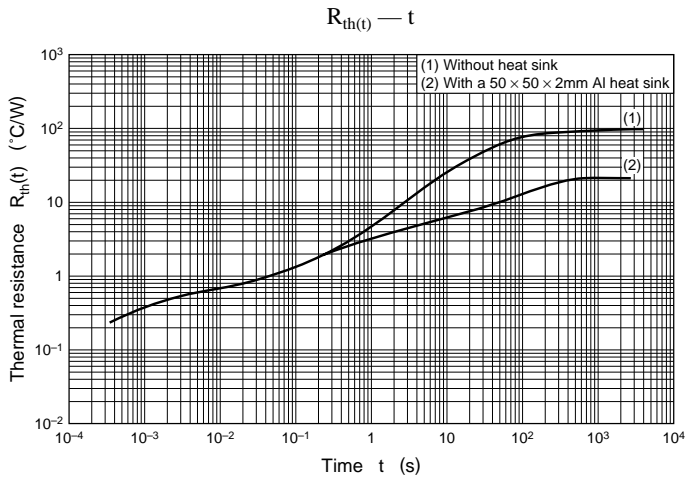


$t_{on}, t_{stg}, t_f - I_C$



Area of safe operation (ASO)





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Datasheets for electronics components.